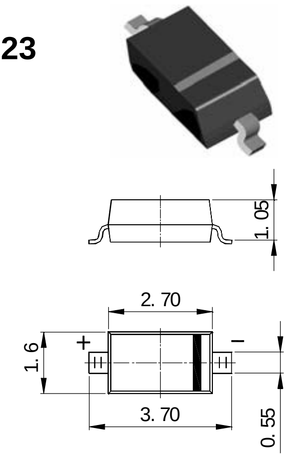
SOD-123



Unit: mm

B5817W SCHOTTKY BARRIER DIODE

FEATURES

Power dissipation

P_D: 450 mW (Tamb=25℃)

Collector current

I_F: 1 A

Collector-base voltage

V_R: 20 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

MARKING: SJ

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	I_R= 1mA	20		V
Reverse voltage leakage current	I_R	V_R=20V		1	mA
Forward voltage	V_F	I_F=1A I_F=3A		0.45 0.75	V
Diode capacitance	C_D	V_R=4V, f=1MHz		120	pF